



CHUANGYUAN TECHNOLOGES (HK) LIMITED

SOT-23-3L Plastic-Encapsulate Diode

1N5817, 1N5819 SCHOTTKY DIODE

FEATURES

Power dissipation

P_D : 300 mW ($T_a=25^\circ\text{C}$)

Collector current

I_F : 1 A

Collector-base voltage

V_R : 1N5817: 20 V

1N5819: 40 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to $+150^\circ\text{C}$

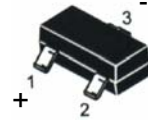
1N5817 Marking: **SJ**

1N5819 Marking: **SL**

SOT-23-3L

1. ANODE

3.CATHODE



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=1\text{mA}$ 1N5817 1N5819	20 40		V
Reverse voltage leakage current	I_R	$V_R=20\text{V}$ $V_R=40\text{V}$		1	μA
Forward voltage	V_F	$I_F=1\text{A}^*$ 1N5817 $I_F=1\text{A}^*$ 1N5819 $I_F=3\text{A}^*$ 1N5817 $I_F=3\text{A}^*$ 1N5819		0.45 0.6 0.75 0.9	V
Diode capacitance	C_D	$V_R=0\text{V}$ $f=1\text{MHz}$		120	pF

* pulse test.

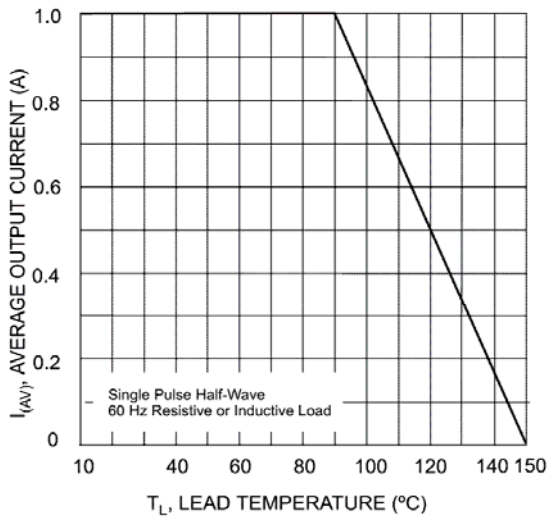


Fig. 1 Forward Current Derating Curve

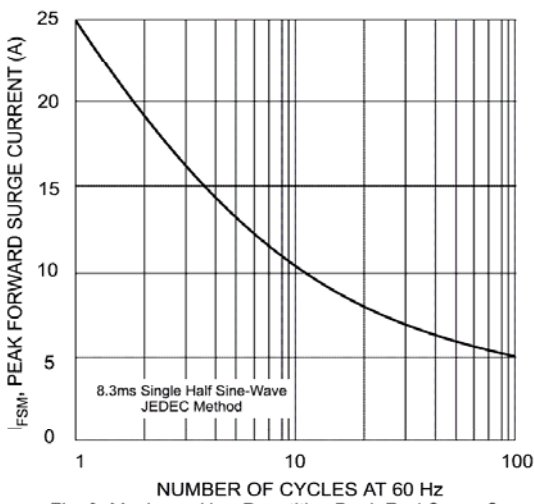
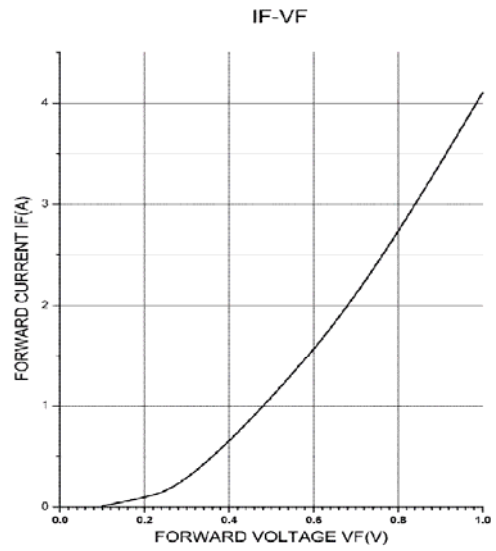


Fig. 3 Maximum Non-Repetitive Peak Fwd Surge Current

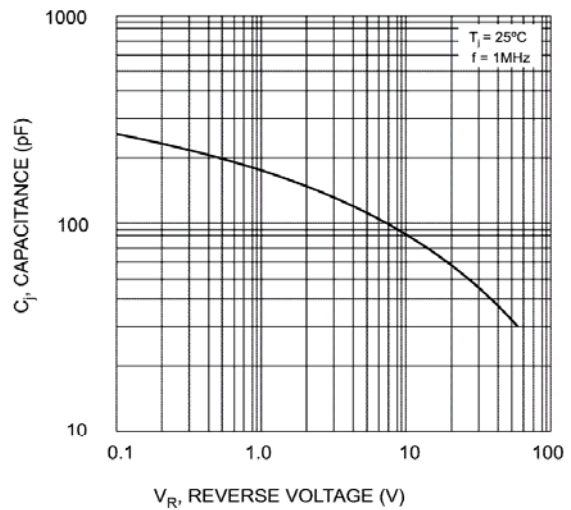


Fig. 4 Typical Junction Capacitance